

### FEATURES

- CTR Minimum at  $I_F = 1 \text{ mA}$   
H11B1, 500%  
H11B2, 200%  
H11B3, 100%
- Isolation Test Voltage, 5300 VAC<sub>RMS</sub>
- Coupling Capacitance, 0.5 pF
- Underwriters Lab File #E52744
-  VDE Approval #0884 (Available with Option 1)

### DESCRIPTION

The H11B1/H11B2/H11B3 are industry standard optocouplers, consisting of a Gallium Arsenide infrared LED and a silicon photodarlington. These optocouplers are constructed with a high voltage insulation, double molded packaging process which offers 7.5 KV withstand test capability.

### Maximum Ratings

#### Emitter

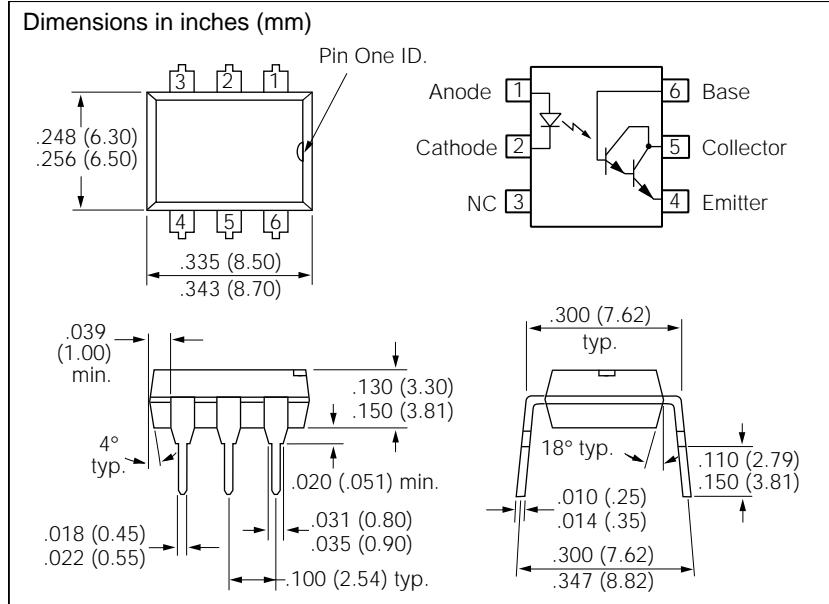
Reverse Voltage .....	3 V
Continuous Forward Current .....	60 mA
Power Dissipation at 25°C .....	100 mW
Derate Linearly from 25°C .....	1.33 mW/°C

#### Detector

Collector-Emitter Breakdown Voltage, $BV_{CEO}$ .....	25 V
Emitter-Collector Breakdown Voltage $BV_{ECO}$ .....	7 V
Collector-Base Breakdown Voltage, $BV_{CBO}$ .....	30 V
Collector-Current (Continuous) .....	100 mA
Power Dissipation at 25°C .....	150 mW
Derate Linearly from 25°C .....	2.0 mW/°C

#### Package

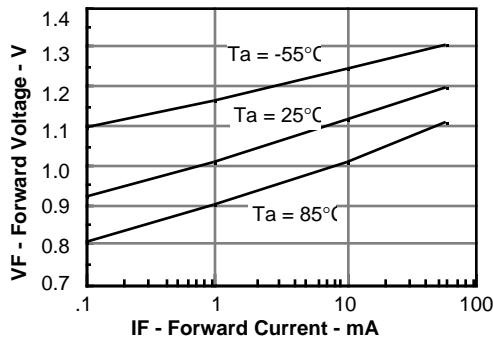
Isolation Test Voltage (between emitter and detector refer to standard climate 23°C/50%RH, DIN 50014) .....	5300 VAC <sub>RMS</sub>
Creepage .....	min. 7 mm
Clearance .....	min. 7 mm
Comparative Tracking Index per DIN IEC 112/VDE 0303, part 1 .....	175
Isolation Resistance	
$V_{IO}=500 \text{ V}, T_A=25^\circ\text{C}$ .....	$\geq 10^{12} \Omega$
$V_{IO}=500 \text{ V}, T_A=100^\circ\text{C}$ .....	$\geq 10^{11} \Omega$
Total Package Dissipation at 25°C (LED plus Detector) .....	260 mW
Derate Linearly from 25°C .....	3.5 mW/°C
Storage Temperature .....	-55°C to +150°C
Operating Temperature .....	-55°C to +100°C
Lead Soldering Time at 260°C .....	10 sec.



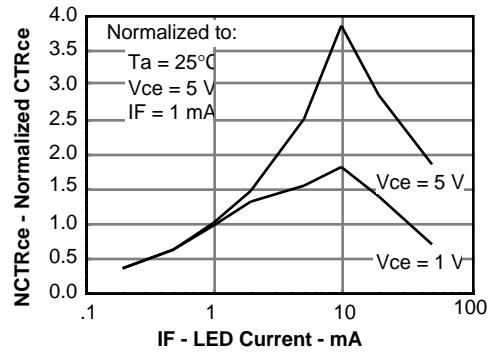
### Characteristics ( $T_A=25^\circ\text{C}$ )

	Sym	Min.	Typ.	Max.	Unit	Condition
<b>Emitter</b>						
Forward Voltage H11B1, B2 H11B3	$V_F$ $V_F$		1.1 1.1	1.5 1.5	V V	$I_F=10 \text{ mA}$ , $I_F=50 \text{ mA}$
Reverse Current	$I_R$			10	$\mu\text{A}$	$V_R=3\text{V}$
Junction Capacitance	$C_J$		50		pF	$V_F=0 \text{ V}$ , $f=1 \text{ mHz}$
<b>Detector</b>						
$BV_{CEO}$		30			V	$I_C=1.0 \text{ mA}$ , $I_F=0 \text{ mA}$
$BV_{ECO}$		7			V	$I_E=100 \mu\text{A}$ , $I_F=0 \text{ mA}$
$BV_{CBO}$		30			V	$I_C=100 \mu\text{A}$ , $I_F=0 \text{ mA}$
$I_{CEO}$				100	nA	$V_{CE}=10 \text{ V}$ , $I_F=0 \text{ mA}$
<b>Package</b>						
$V_{CEsat}$				1.0		$I_C=1 \text{ mA}$ , $I_C=1 \text{ mA}$
DC Current Transfer Ratio H11B1 H11B2 H11B3	CTR CTR CTR	500 200 100			%	$V_{CE}=5 \text{ V}$ , $I_F=1 \text{ mA}$ $V_{CE}=5 \text{ V}$ , $I_F=1 \text{ mA}$ $V_{CE}=5 \text{ V}$ , $I_F=1 \text{ mA}$
Capacitance Input to Output	$C_{IO}$		0.5		pF	
Switching Times	$t_{on}$ $t_{off}$		5 30		$\mu\text{s}$ $\mu\text{s}$	$I_F=5 \text{ mA}$ $V_{CE}=10 \text{ V}$ $R_L=100 \Omega$

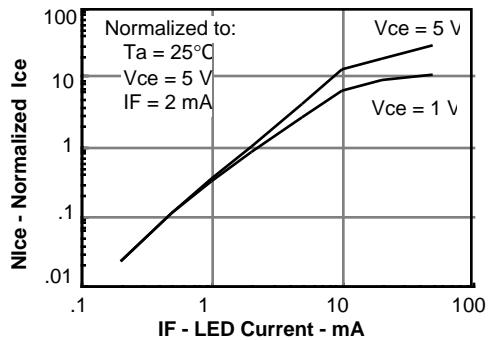
**Figure 1. Forward voltage versus forward current**



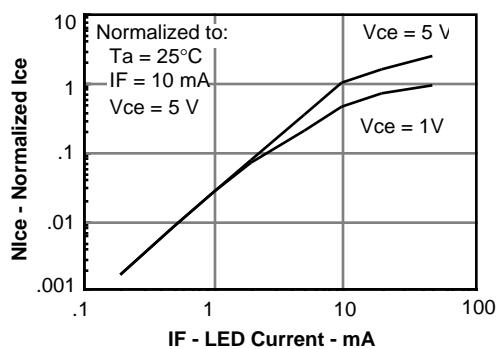
**Figure 2. Normalized non-saturated and saturated CTR<sub>ce</sub> versus LED current**



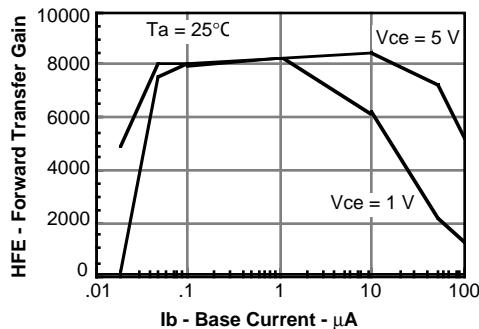
**Figure 3. Normalized non-saturated and saturated ICE versus LED current**



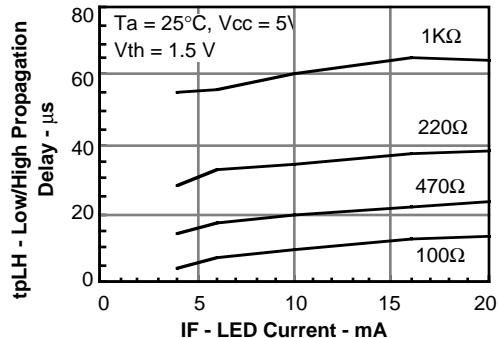
**Figure 4. Normalized non-saturated and saturated collector-emitter current versus LED current**



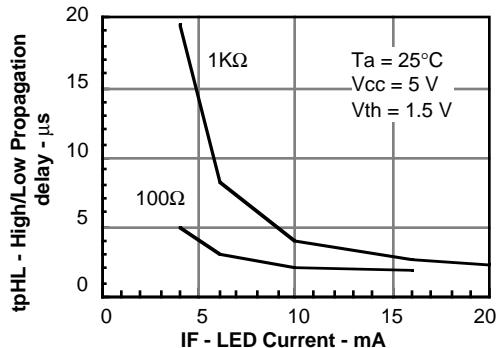
**Figure 5. Non-saturated and saturated HFE versus base current**



**Figure 6. Low to high propagation delay versus collector load resistance and LED current**



**Figure 7. High to low propagation delay versus collector load resistance and LED current**



**Figure 8. Switching waveform and schematic**

